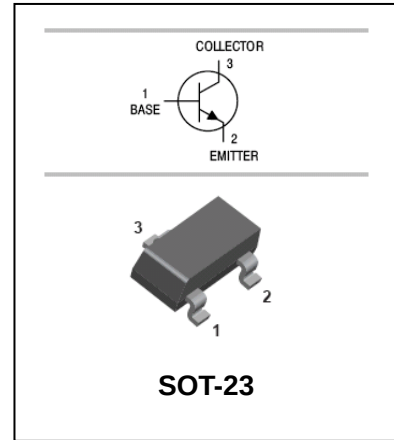


## Silicon Epitaxial Planar Transistor

## 2SC2859

### FEATURES

- Power dissipation:  $P_C=150\text{mW}$ .
- Excellent  $h_{FE}$  linearity:  $h_{FE(2)}=25$   
( $V_{CE}=6\text{V}, I_C=400\text{mA}$ )
- Complementary to 2SA1182.



### APPLICATIONS

- Audio frequency general purpose amplifier applications.

### ORDERING INFORMATION

| Type No. | Marking  | Package Code |
|----------|----------|--------------|
| 2SC2859  | WO/WY/WG | SOT-23       |

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| Symbol         | Parameter                        | Value   | Units            |
|----------------|----------------------------------|---------|------------------|
| $V_{CBO}$      | Collector-Base Voltage           | 35      | V                |
| $V_{CEO}$      | Collector-Emitter Voltage        | 30      | V                |
| $V_{EBO}$      | Emitter-Base Voltage             | 5       | V                |
| $I_C$          | Collector Current -Continuous    | 500     | mA               |
| $P_C$          | Collector Dissipation            | 150     | mW               |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -55~125 | $^\circ\text{C}$ |

**Silicon Epitaxial Planar Transistor****2SC2859****ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified**

| Parameter                            | Symbol        | Test conditions                                  | MIN      | TYP | MAX  | UNIT    |
|--------------------------------------|---------------|--------------------------------------------------|----------|-----|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=100\mu A, I_E=0$                            | 35       |     |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=1mA, I_B=0$                                 | 30       |     |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=100\mu A, I_C=0$                            | 5        |     |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=35V, I_E=0$                              |          |     | 0.1  | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=5V, I_C=0$                               |          |     | 0.1  | $\mu A$ |
| DC current gain                      | $h_{FE}$      | $V_{CE}=1V, I_C=100mA$<br>$V_{CE}=6V, I_C=400mA$ | 70<br>25 |     | 400  |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=100mA, I_B=10mA$                            |          | 0.1 | 0.25 | V       |
| Base-emitter voltage                 | $V_{BE}$      | $V_{CE}=1V, I_C=100mA$                           |          | 0.8 | 1.0  | V       |
| Collector output capacitance         | $C_{ob}$      | $V_{CB}=6V, I_E=0, f=1MHz$                       |          | 7   |      | pF      |
| Transition frequency                 | $f_T$         | $V_{CE}=6V, I_C=20mA$                            |          | 300 |      | MHz     |

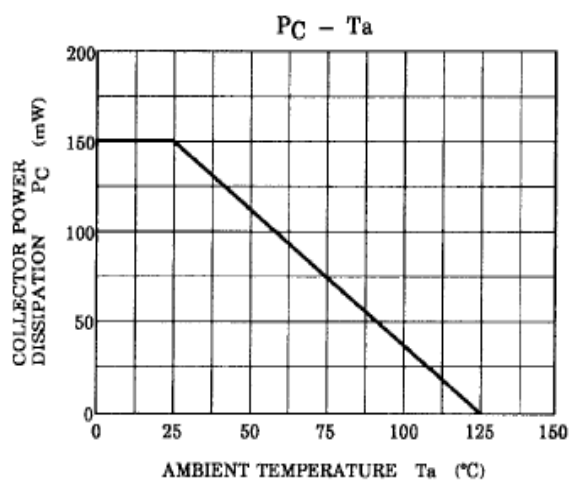
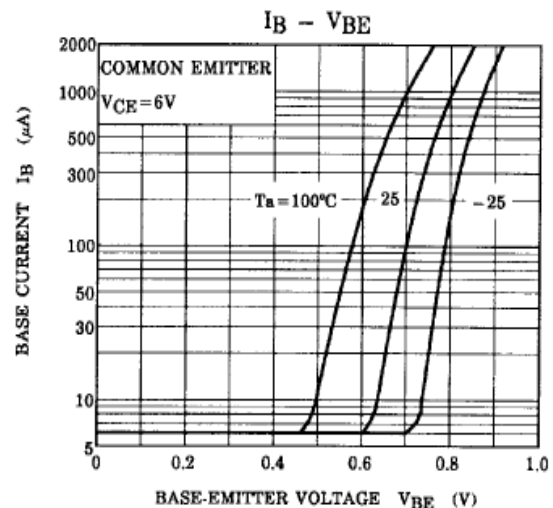
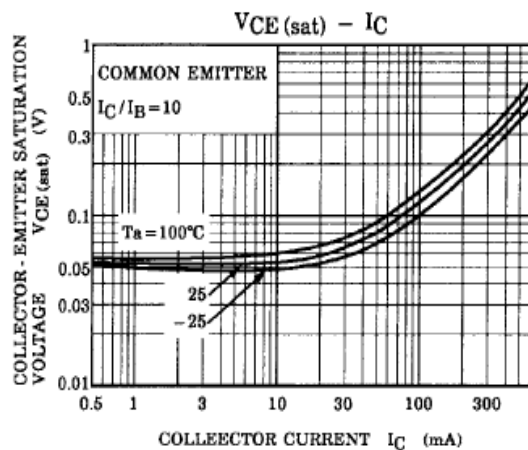
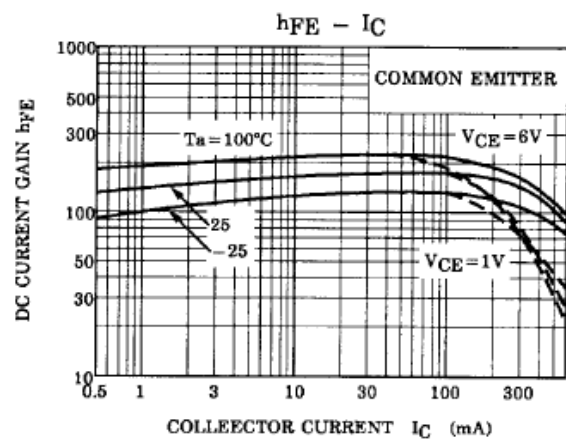
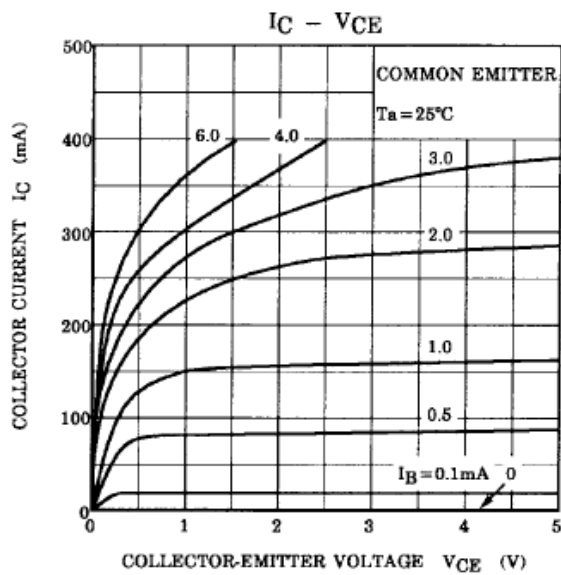
**CLASSIFICATION OF  $h_{FE(1)}$** 

| Rank  | O      | Y       | G       |
|-------|--------|---------|---------|
| Range | 70-140 | 120-240 | 200-400 |

**TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified**

## Silicon Epitaxial Planar Transistor

## 2SC2859



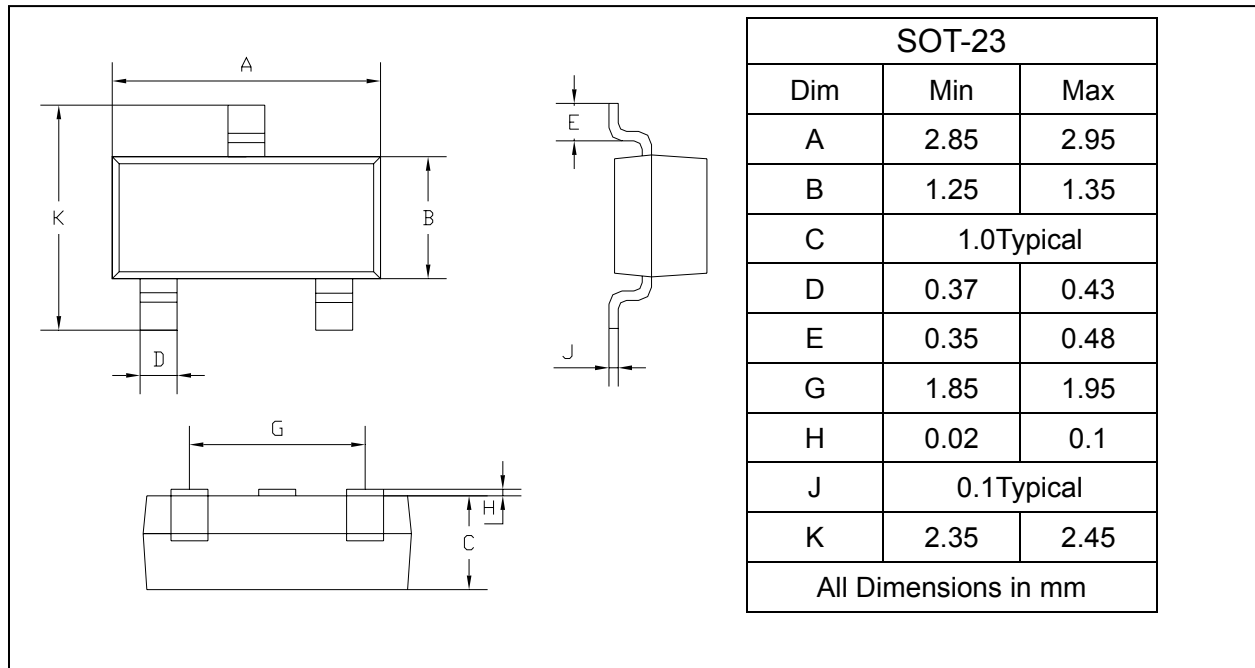
## Silicon Epitaxial Planar Transistor

**2SC2859**

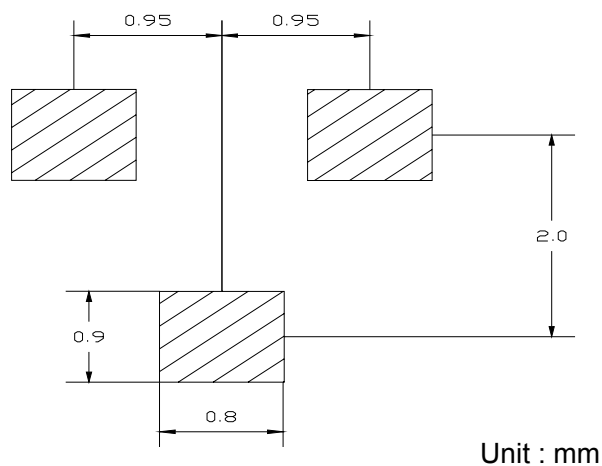
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device  | Package | Shipping       |
|---------|---------|----------------|
| 2SC2859 | SOT-23  | 3000/Tape&Reel |